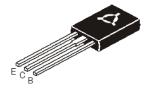
# NPN Transistor TO-126





**Pin Configuration:** 

1. Emitter

2. Collector

3. Base

## **Absolute Maximum Ratings**

Description	Symbol	BD139	Unit	
Collector-emitter voltage	V <sub>CEO</sub>	80		
Collector-emitter voltage ( $R_{BE} = 1k\Omega$ )	V <sub>CER</sub>	100	V	
Collector-base voltage	V <sub>CBO</sub>	100		
Emitter base voltage	V <sub>EBO</sub>	5		
Collector current	Ι <sub>C</sub>	1.5		
Collector peak current	I <sub>CM</sub>	2	A	
Base current	I <sub>B</sub>	0.5		
Power dissipation at T <sub>a</sub> = 25°C Derate above 25°C	Р	1.25 10	W mW/ºC	
Power dissipation at T <sub>c</sub> = 25°C Derate above 25°C	Р	12.5 100	W mW/ºC	
Power dissipation at $T_c = 70^{\circ}C$	P <sub>D</sub>	8	W	
Operating and storage junction Temperature range	T <sub>j</sub> , T <sub>stg</sub>	-55 to +150	°C	

#### Thermal Characteristics

Junction to ambient in free air	R <sub>th (j-a)</sub>	100	°C/W
Junction to case	R <sub>th (j-c)</sub>	10	°C/W

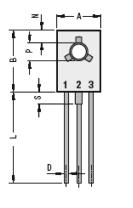
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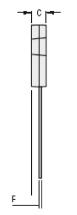


## Electrical characteristics (Tc = 25°C unless specified otherwise)

Description	Symbol	Test Condition	Min.	Max.	Unit
Collector emitter sustaining voltage	*V <sub>CEO (sus)</sub>	I <sub>C</sub> = 30mA, I <sub>B</sub> = 0	80		V
		V <sub>CB</sub> = 30V, I <sub>E</sub> = 0		0.1	
Collector cut off current	I <sub>CBO</sub>	V <sub>CB</sub> = 30V, I <sub>E</sub> = 0, T = 125°C		10	μA
Emitter cut off current	I <sub>EBO</sub>	V <sub>EB</sub> = 5V, I <sub>C</sub> = 0			
DC current gain	*h <sub>FE</sub>	$    I_{C} = 0.005A, V_{CE} = 2V \\     I_{C} = 0.15A, V_{CE} = 2V \\     I_{C} = 0.5A, V_{CE} = 2V $	25 40 25	250	-
Collector emitter sustaining voltage	*V <sub>CEO (sus)</sub>	I <sub>C</sub> = 30mA, I <sub>B</sub> = 0 BD139	80		V
		V <sub>CB</sub> = 30V, I <sub>E</sub> = 0		0.1	
Collector cut off current	I <sub>CBO</sub>	V <sub>CB</sub> = 30V, I <sub>E</sub> = 0, T = 125°C		10	μA
Emitter cut off current	I <sub>EBO</sub>	V <sub>EB</sub> = 5V, I <sub>C</sub> = 0			
DC current gain	*h <sub>FE</sub>	$ \begin{array}{l} I_{C} = 0.005 \text{A},  V_{CE}  =  2 \text{V} \\ I_{C} = 0.15 \text{A},  V_{CE}  =  2 \text{V} \\ I_{C} = 0.5 \text{A},  V_{CE}  =  2 \text{V} \end{array} $	25 40 25	250	-

\*Pulse test: -Pulse width=300ms, duty cycle = 2%.





Pin Configuration:

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Dimensions	Min.	Max.
А	7.2	8.38
В	10.16	11.43
С	2.29	3.04
D	0.64	0.88
E	2.04	2.285
F	0.39	0.63
G	4.07	5.08
L	15	16.63
М	0.89	1.65
Ν	3.31	4.44
Р	2.54	3.3
S	-	2.54

**Dimensions : Millimetres** 

### Part Number Table

Description	Part Number
Transistor, NPN, TO-126	BD139-10

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